

NOT entered
DW 8/4/05

SN/10/695,432
1153.078US1

1. (Currently Amended) A sensor comprising:
a field effect transistor having a source, drain and floating gate, wherein the floating gate has an extended portion;
a control gate electrostatically coupled to the floating gate; and
a chemoreceptive layer coupled to the ~~extended portion of the floating~~ control gate.
10. (Currently Amended) A sensor comprising:
a field effect transistor having a source, drain and floating gate, wherein the floating gate has an extended portion; and
multiple control gates capacitively coupled to the extended portion of the floating gate.
11. (Original) The sensor of claim 10 wherein some of the control gates comprise chemoreceptive fingers capacitively coupled to the floating gate.

I did not amend claim 10 because Au does not show that the control gates are capacitively coupled to an extended portion of a floating gate. In Au, it appears that each control gate is actually a gate that directly affects current flow. There is no extension of the gate that is then capacitively coupled to control gates. Please give me a call to discuss if this does not overcome your reservations about this claim.

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